

# SKiiP 11AC12T4V1



MiniSKiiP® 1

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### Features\*

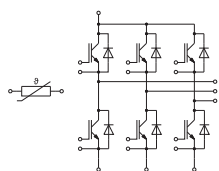
- Trench 4 IGBTs
- Robust and soft switching freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532

### Typical Applications

- Inverter up to 8 kVA
- Typical motor power 4 kW

### Remarks

- $V_{CEsat}$ ,  $V_F$  = chip level value
- Case temp. limited to  $T_C = 125^\circ\text{C}$  max. (for baseplateless modules  $T_C = T_S$ )
- product rel. results valid for  $T_J \leq 150$  (recomm.  $T_{op} = -40 \dots +150^\circ\text{C}$ )



AC

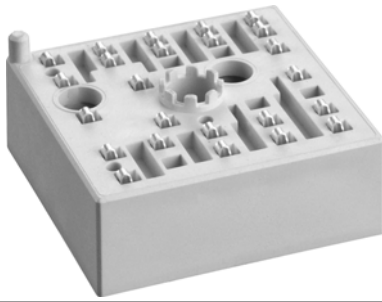
### Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
Inverter - IGBT				
V <sub>CES</sub>	T <sub>j</sub> = 25 °C		1200	V
I <sub>C</sub>	λ <sub>paste</sub> =0.8 W/(mK)	T <sub>s</sub> = 25 °C	12	A
	T <sub>j</sub> = 175 °C	T <sub>s</sub> = 70 °C	12	A
I <sub>C</sub>	λ <sub>paste</sub> =2.5 W/(mK)	T <sub>s</sub> = 25 °C	19	A
	T <sub>j</sub> = 175 °C	T <sub>s</sub> = 70 °C	16	A
I <sub>Cnom</sub>			8	A
I <sub>CRM</sub>			24	A
V <sub>GES</sub>			-20 ... 20	V
t <sub>psc</sub>	V <sub>CC</sub> = 800 V V <sub>GE</sub> ≤ 15 V V <sub>CES</sub> ≤ 1200 V	T <sub>j</sub> = 150 °C	10	µs
T <sub>j</sub>			-40 ... 175	°C
Inverse - Diode				
V <sub>RRM</sub>	T <sub>j</sub> = 25 °C		1200	V
I <sub>F</sub>	λ <sub>paste</sub> =0.8 W/(mK)	T <sub>s</sub> = 25 °C	15	A
	T <sub>j</sub> = 175 °C	T <sub>s</sub> = 70 °C	12	A
I <sub>F</sub>	λ <sub>paste</sub> =2.5 W/(mK)	T <sub>s</sub> = 25 °C	17	A
	T <sub>j</sub> = 175 °C	T <sub>s</sub> = 70 °C	13	A
I <sub>FRM</sub>			24	A
I <sub>FSM</sub>	t <sub>p</sub> = 10 ms, sin 180°, T <sub>j</sub> = 150 °C		36	A
T <sub>j</sub>			-40 ... 175	°C
Module				
I <sub>t(RMS)</sub>	T <sub>terminal</sub> = 80 °C, 20 A per spring		20	A
T <sub>stg</sub>	module without TIM		-40 ... 125	°C
V <sub>isol</sub>	AC sinus 50 Hz, t = 1 min		2500	V

### Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
<b>Inverter - IGBT</b>					
$V_{CE(sat)}$	$I_C = 8 \text{ A}$ $V_{GE} = 15 \text{ V}$ chipelevel	$T_J = 25^\circ\text{C}$	1.85	2.10	V
		$T_J = 150^\circ\text{C}$	2.25	2.45	V
$V_{CE0}$	chipelevel	$T_J = 25^\circ\text{C}$	0.80	0.90	V
		$T_J = 150^\circ\text{C}$	0.70	0.80	V
$r_{CE}$	$V_{GE} = 15 \text{ V}$ chipelevel	$T_J = 25^\circ\text{C}$	131	150	m $\Omega$
		$T_J = 150^\circ\text{C}$	194	206	m $\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 1 \text{ mA}$	5	5.8	6.5	V
$I_{CES}$	$V_{GE} = 0 \text{ V}, V_{CE} = 1200 \text{ V}, T_J = 25^\circ\text{C}$			1	mA
$C_{ies}$	$V_{CE} = 25 \text{ V}$	$f = 1 \text{ MHz}$	0.49		nF
$C_{oes}$	$V_{GE} = 0 \text{ V}$	$f = 1 \text{ MHz}$	0.05		nF
$C_{res}$		$f = 1 \text{ MHz}$	0.03		nF
$Q_G$	$V_{GE} = -8 \text{ V} \dots +15 \text{ V}$		45		nC
$R_{Gint}$	$T_J = 25^\circ\text{C}$		0		$\Omega$
$t_{d(on)}$	$V_{CC} = 600 \text{ V}$	$T_J = 150^\circ\text{C}$	32		ns
$t_r$	$I_C = 8 \text{ A}$ $R_{Gon} = 56 \Omega$	$T_J = 150^\circ\text{C}$	28		ns
		$T_J = 150^\circ\text{C}$	0.87		mJ
$E_{on}$	$R_{Goff} = 56 \Omega$	$T_J = 150^\circ\text{C}$			mJ
$t_{d(off)}$	$di/dt_{on} = 280 \text{ A}/\mu\text{s}$	$T_J = 150^\circ\text{C}$	300		ns
$t_f$	$di/dt_{off} = 90 \text{ A}/\mu\text{s}$	$T_J = 150^\circ\text{C}$	65		ns
$E_{off}$	$V_{GE} = +15/-15 \text{ V}$	$T_J = 150^\circ\text{C}$	0.75		mJ
$R_{th(j-s)}$	per IGBT, $\lambda_{paste}=0.8 \text{ W/(mK)}$		1.84		K/W
$R_{th(j-s)}$	per IGBT, $\lambda_{paste}=2.5 \text{ W/(mK)}$		1.58		K/W

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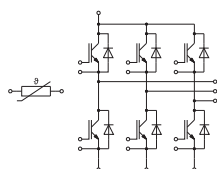
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- Case temp. limited to  $T_C = 125^\circ\text{C}$  max. (for baseplateless modules  $T_C = T_S$ )
- product rel. results valid for  $T_j \leq 150$  (recomm.  $T_{op} = -40 \dots +150^\circ\text{C}$ )

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse - Diode						
V <sub>F</sub> = V <sub>EC</sub>	I <sub>F</sub> = 8 A	T <sub>j</sub> = 25 °C		2.33	2.65	V
	V <sub>GE</sub> = 0 V	T <sub>j</sub> = 150 °C		2.35	2.68	V
	chiplevel					
V <sub>F0</sub>		T <sub>j</sub> = 25 °C		1.30	1.50	V
	chiplevel	T <sub>j</sub> = 150 °C		0.90	1.10	V
r <sub>F</sub>		T <sub>j</sub> = 25 °C		129	144	mΩ
	chiplevel	T <sub>j</sub> = 150 °C		181	198	mΩ
I <sub>RRM</sub>	I <sub>F</sub> = 8 A	T <sub>j</sub> = 150 °C		7.7		A
Q <sub>rr</sub>	di/dt <sub>off</sub> = 350 A/μs	T <sub>j</sub> = 150 °C		1.3		μC
E <sub>rr</sub>	V <sub>GE</sub> = +15/-15 V	T <sub>j</sub> = 150 °C		0.53		mJ
	V <sub>CC</sub> = 600 V					
R <sub>th(j-s)</sub>	per Diode, λ <sub>paste</sub> =0.8 W/(mK)			2.53		K/W
R <sub>th(j-s)</sub>	per Diode, λ <sub>paste</sub> =2.5 W/(mK)			2.19		K/W
Module						
L <sub>CE</sub>				-		nH
M <sub>s</sub>	to heat sink		2		2.5	Nm
w				30		g
Temperature Sensor						
R <sub>100</sub>	T <sub>r</sub> =100°C (R <sub>25</sub> =1000Ω)			1670 ± 3%		Ω
R <sub>(T)</sub>	R <sub>(T)</sub> =1000Ω[1+A(T-25°C)+B(T-25°C) <sup>2</sup> ] , A = 7.635*10 <sup>-3</sup> °C <sup>-1</sup> , B = 1.731*10 <sup>-5</sup> °C <sup>-2</sup>					



AC

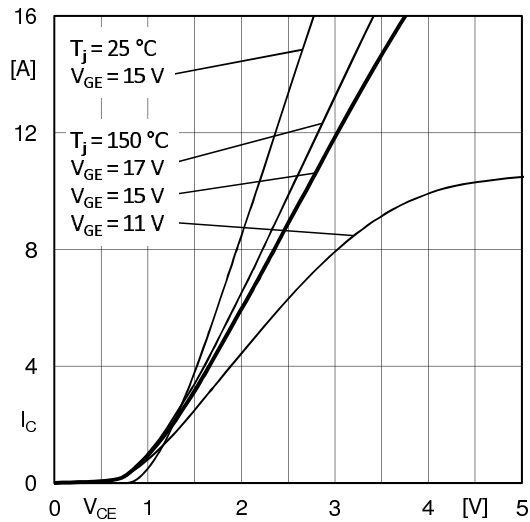


Fig. 1: Typ. output characteristic

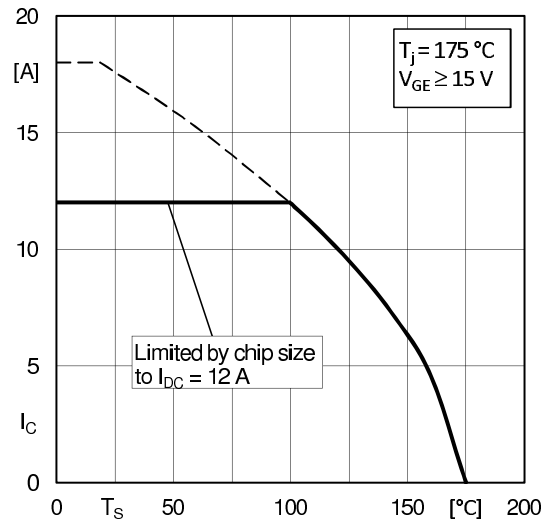


Fig. 2: Rated current vs. temperature  $I_C = f(T_S)$

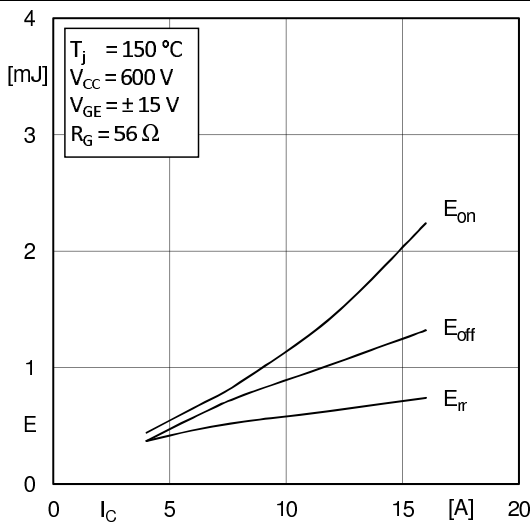


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$

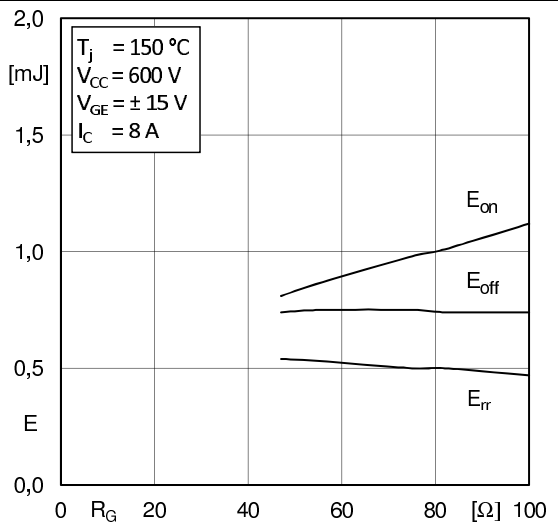


Fig. 4: Typ. turn-on /-off energy =  $f(R_G)$

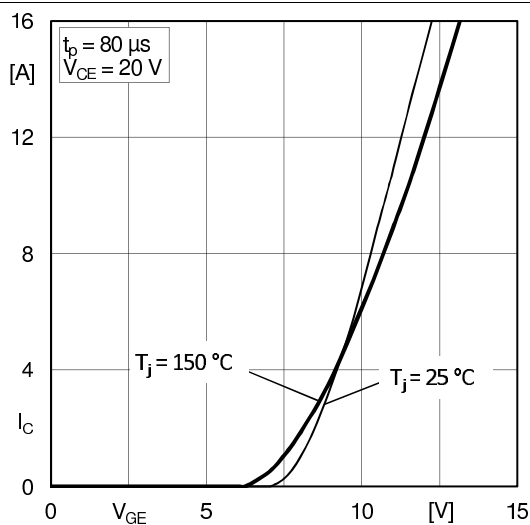


Fig. 5: Typ. transfer characteristic

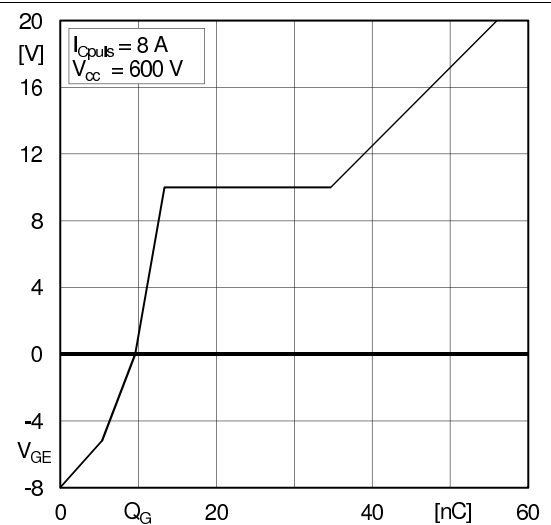


Fig. 6: Typ. gate charge characteristic

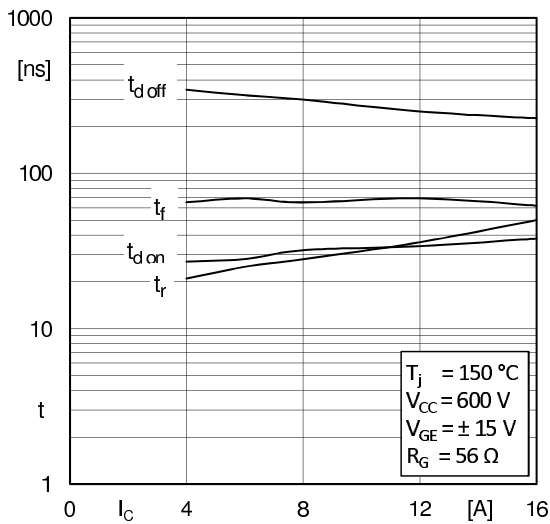


Fig. 7: Typ. switching times vs.  $I_C$

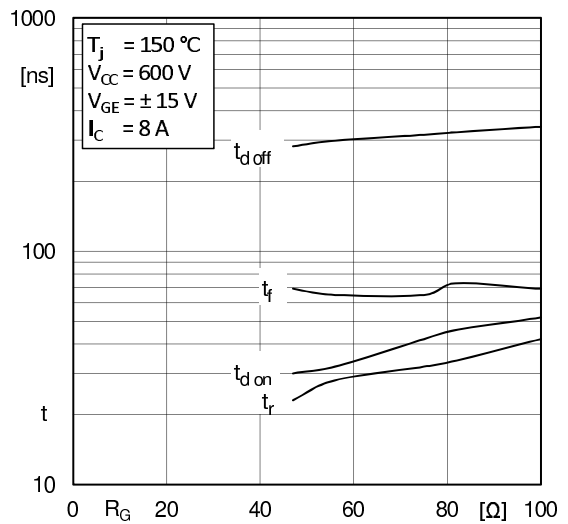


Fig. 8: Typ. switching times vs. gate resistor  $R_G$

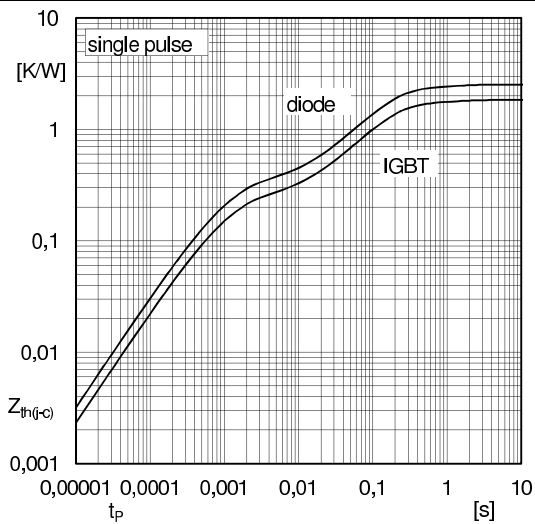


Fig. 9: Typ. transient thermal impedance

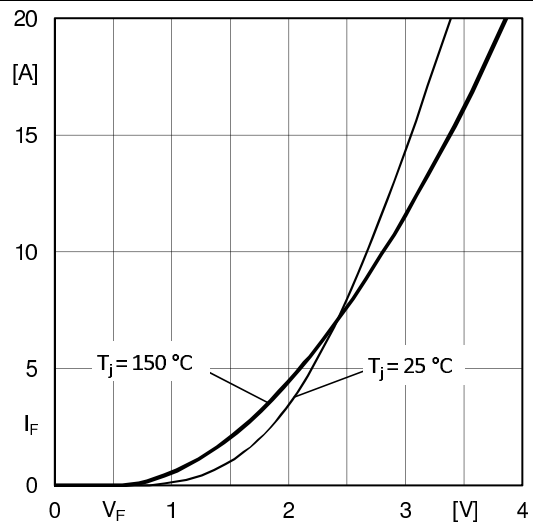


Fig. 10: Typ. CAL diode forward characteristic

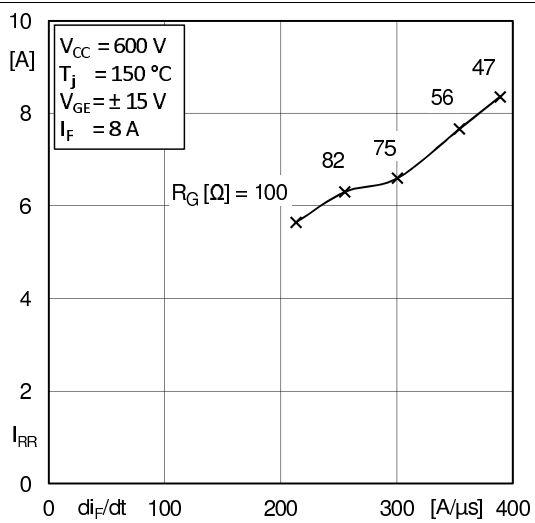


Fig. 11: Typ. CAL diode peak reverse recovery current

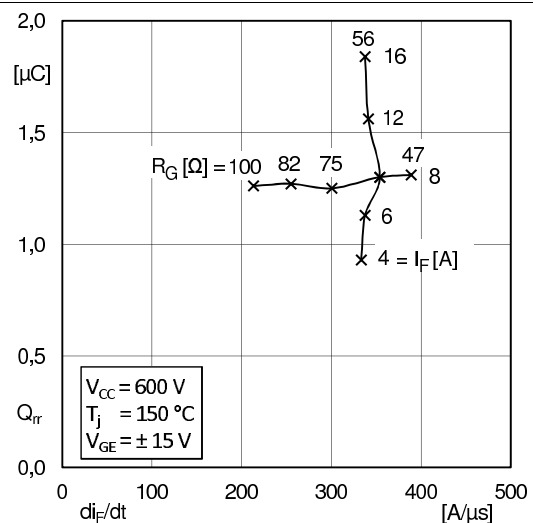
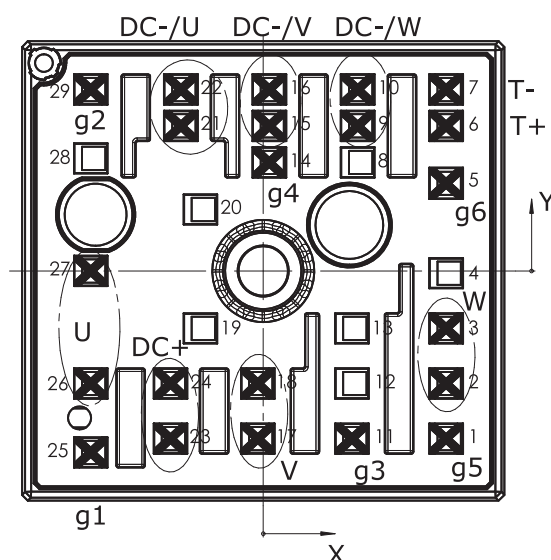


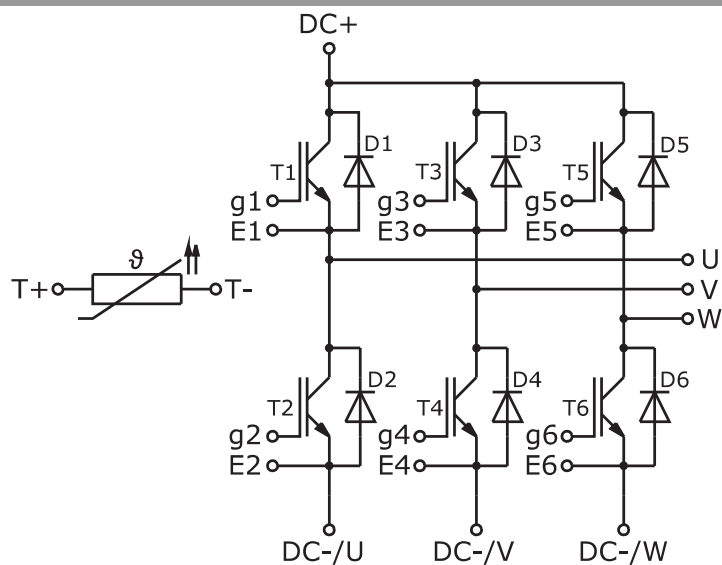
Fig. 12: Typ. CAL diode recovery charge

Pin out							
Pin	X	Y	Function	Pin	X	Y	Function
1	15,93	-14,60	g5	16	0,53	15,80	DC-/V
2	15,93	-9,80	W	17	-0,48	-14,6	V
3	15,93	-5,00	W	18	-0,48	-9,80	V
4	15,93	-0,20		19	-5,48	-5,00	
5	15,93	7,63	g6	20	-5,48	5,35	
6	15,93	12,63	T+	21	-7,18	12,63	DC-/U
7	15,93	15,80	T-	22	-7,18	15,80	DC-/U
8	8,23	9,45		23	-8,08	-14,60	DC+
9	8,23	12,63	DC-/W	24	-8,08	-9,80	DC+
10	8,23	15,80	DC-/W	25	-15,03	-15,80	g1
11	7,73	-14,60	g3	26	-15,03	-9,80	U
12	7,73	-9,80		27	-15,03	0	U
13	7,73	-5,00		28	-15,03	9,80	
14	0,53	9,45	g4	29	-15,03	15,80	g2
15	0,53	12,63	DC-/V				

all values in mm



Pinout and Dimensions



Pinout

This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

## **\*IMPORTANT INFORMATION AND WARNINGS**

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